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PTO/SB/08A (10-01)

Approved for use through 10/31/2002. OMB 0651-0031

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<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)				<b>Complete if Known</b>	
				Application Number	09/296,835
				Filing Date	April 22, 1999
				First Named Inventor	Ronald A. Weimer
				Art Unit	2813
				Examiner Name	E. Kielin
Sheet	1	of	1	Attorney Docket Number	M4065.0319/P319

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number Number-Kind Code <sup>2</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
ER	A	6,063,698	05/16/00	Tseng et al.	
ER	B	6,197,668	03/06/01	Gardner, et al.	
ER	C	US-2001/0020725	09/13/01	Okuno, et al.	

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
		Country Code <sup>3</sup> -Number <sup>4</sup> -Kind Code <sup>5</sup> (if known)				

<sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> See attached Kinds Codes of USPTO Patent Documents at [www.uspto.gov](http://www.uspto.gov) or MPEP 901.04. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup> Applicant is to place a check mark here if English language Translation is attached.

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
ER	D	LU, et al., "Leakage Current Comparison Between Ultra-Thin Ta <sub>2</sub> O <sub>5</sub> films and conventional gate dielectrics" IEEE Electron Device Letters 19(9), 9/1998, pp. 341-342	
ER	E	ALERS, et al., "Intermixing at the Tantalum Oxide/Silicon Interface in Gate Dielectric Structures" Applied Physics Letters 73(11), 14 September 1998, pp. 1517-1519	
ER	F	LUAN, et al., "Ultra-thin High Quality Ta <sub>2</sub> O <sub>5</sub> Dielectric Prepared by In-Situ Rapid Thermal Processing" Electron Devices Meeting, held 6-9 December 1998, IEDM '98 Technical Digest, pp. 609-612.	

Examiner Signature		Date Considered	6/14/03
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